

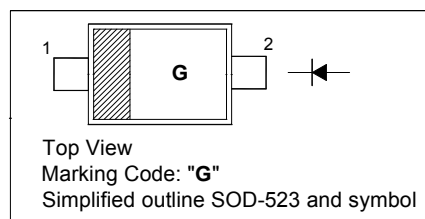
SCHOTTKY BARRIER DIODE

Features

- Low power rectified
- Silicon epitaxial type
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Forward Current	I_F	0.2	A
Repetitive Peak Forward Current	I_{FRM}	0.5	A
Non-Repetitive Peak Forward Current (10 ms)	I_{FSM}	2	A
Power Dissipation	P_D	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$ at $I_F = 30\text{ mA}$	V_F	0.4 0.5	V
Reverse Current at $V_R = 30\text{ V}$	I_R	1	μA
Total Capacitance at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_T	10	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$, $I_{RR} = 1\text{ mA}$, $R_L = 100\ \Omega$	t_{rr}	5	ns

Fig. 1 $I_F - V_F$

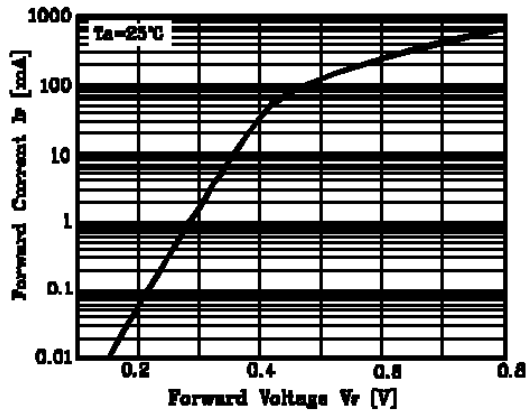


Fig. 2 $I_R - V_R$

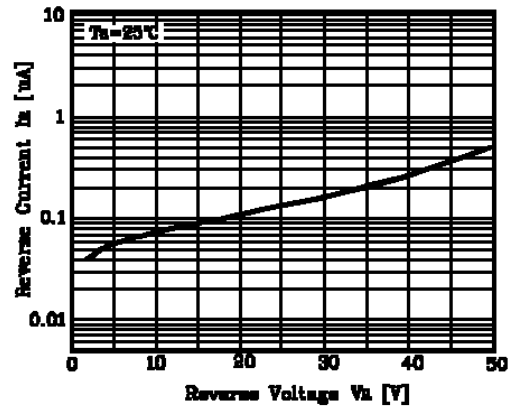
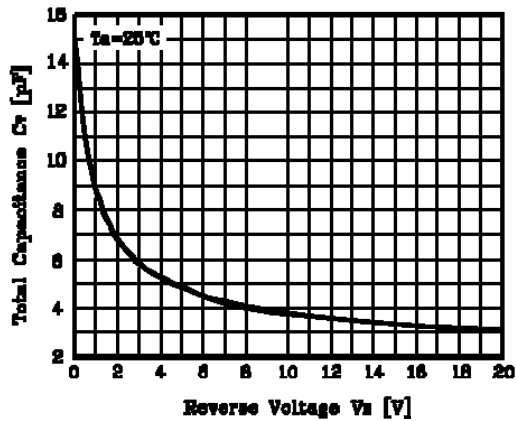


Fig. 3 $C_T - V_R$





CHINA BASE
INTERNATIONAL

SOD-523

SDB310Q

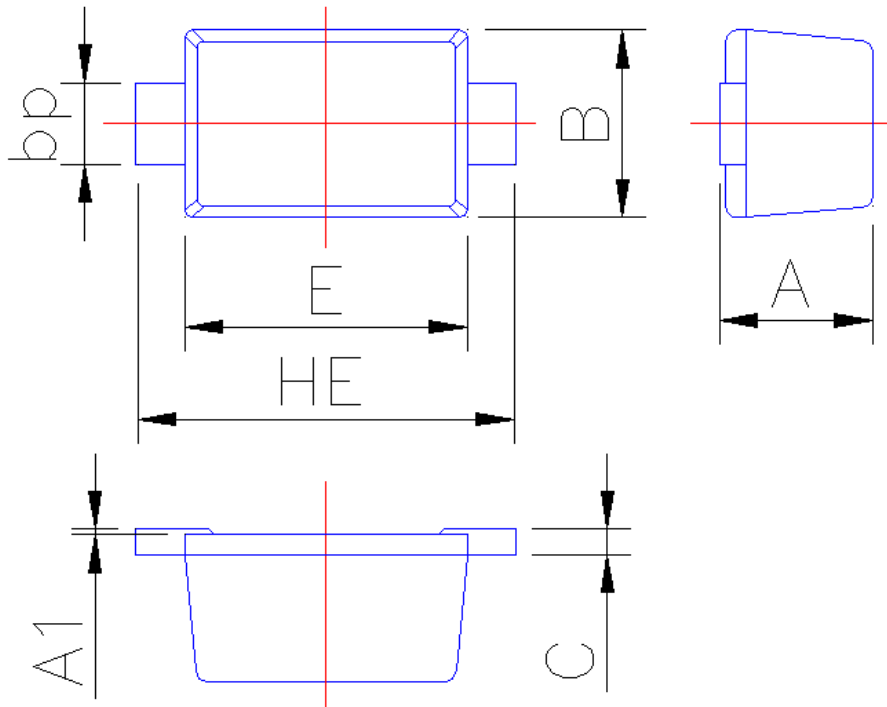


www.china-base.com.hk

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
A1	0	0.05
B	0.75	0.85
bp	0.25	0.40
C	0.09	0.15
E	1.15	1.25
HE	1.50	1.70